

TRAILING EDGE PRODUCT - MINIMUM ORDER APPLIES



2M x 8 SRAM MODULE

SYS82000RKXC - 70/85/10/12

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Description

The SYS82000RKXC is a plastic 16Mbit Static RAM Module housed in a standard 38 pin Single In-Line package organised as 2M x 8 with access times of 70, 85, 100, or 120 ns.

The module is constructed using four 512Kx8 SRAMs in TSOPII packages mounted onto an FR4 epoxy substrate. This offers an extremely high PCB packing density.

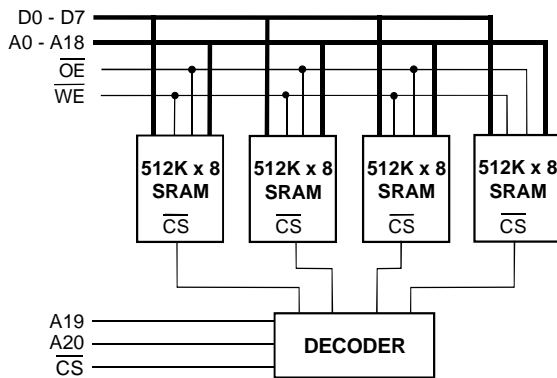
The device is offered in standard and low power versions, with the -L module having a low voltage data retention mode for battery backed applications.

Features

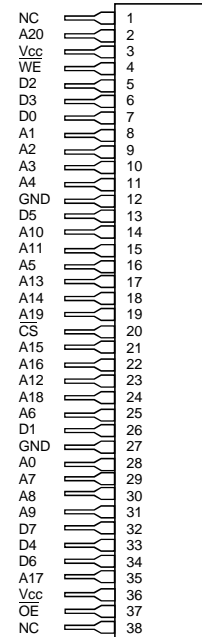
- Access Times of 70/85/100/120 ns.
- Low Power Disipation:

Operating	600 mW (Max.)
Standby-L Version	1.1 mW (Max.)
- 5 Volt Supply $\pm 10\%$.
- Completely Static Operation.
- Low Voltage V_{CC} Data Retention.
- On-board Decoding & Decoupling Capacitors.
- 38 Pin Single-In-Line package (SIP).
- Upgrade path to SYS84000RKXC (32Mbits).

Block Diagram



Pin Definition



Pin 38 is A21 on the
SYS84000RKXC upgrade module.

Pin Functions

Address Inputs	A0 ~ A20
Data Input/Output	D0 ~ D7
Chip Select	CS
Write Enable	WE
Output Enable	OE
No Connect	NC
Power (+5V)	V_{CC}
Ground	GND

Package Details

Plastic 38 pin Single-In-Line (SIP)

DC OPERATING CONDITIONS**Absolute Maximum Ratings** ⁽¹⁾

Parameter	Symbol	min	typ	max	unit
Voltage on any pin relative to V _{SS}	V _T	-0.3	-	+7	V
Power Dissipation	P _T	-	-	4.0	W
Storage Temperature	T _{STG}	-55	-	+125	°C

Notes :

(1) Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

(2) V_T can be -3.0 V pulse of less than 30 ns.

Recommended Operating Conditions

Parameter	Symbol	min	typ	max	unit
Supply Voltage	V _{CC}	4.5	5.0	5.5	V
Input High Voltage	V _{IH}	2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL}	-0.3	-	0.8	V
Operating Temperature	T _A	0	-	70	°C
	T _{AI}	-40	-	85	°C (I)

DC Electrical Characteristics (V_{CC}=5V±10%)T_A 0 to 70°C

Parameter	Symbol	Test Condition	min	typ	max	Unit
I/P Leakage Current	I _{LI}	V _{IN} = GND to V _{CC}	-4	-	4	μA
Output Leakage Current	I _{LO}	$\overline{CS} = V_{IH}$, V _{IO} = GND to V _{CC}	-4	-	4	μA
Operating Supply Current	I _{CC}	$\overline{CS} = V_{IL}$, min cycle, Duty = 100%	-	-	109	mA
Standby Supply Current TTL levels	I _{SB1}	$\overline{CS} = V_{IH}$	-	-	12	mA
	I _{SB2}	$\overline{CS} = V_{CC} - 0.2V$, 0.2 > V _{IN} > V _{CC} - 0.2V	-	-	200	μA
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA	-	-	0.4	V
Output High Voltage	V _{OH}	I _{OH} = -1.0mA	2.4	-	-	V

Capacitance (V_{CC}=5V±10%, T_A=25°C)

Note: Capacitance calculated, not measured.

Parameter	Symbol	Test Condition	typ	max	Unit
Input Capacitance (\overline{CS} , A19, A20)	C _{IN1}	V _{IN} = 0V	-	8	pF
Input Capacitance (A0-18, OE, WE)	C _{IN2}	V _{IN} = 0V	-	32	pF
I/O Capacitance	C _{IO}	V _{IO} = 0V	-	10	pF

Operation Truth Table

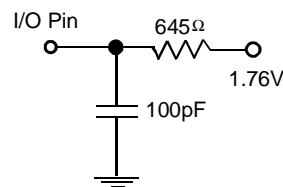
\overline{CS}	\overline{OE}	\overline{WE}	DATA PINS	SUPPLY CURRENT	MODE
H	X	X	High Impedance	I_{SB1}, I_{SB2}	Standby
L	L	H	Data Out	I_{CC}	Read
L	X	L	Data In	I_{CC}	Write
L	H	H	High Impedance	I_{CC}	Output Disabled

Notes : H = V_{IH} : L = V_{IL} : X = V_{IH} or V_{IL}

AC Test Conditions

- * Input pulse levels: 0 V to 3.0V
- * Input rise and fall times: 5ns
- * Input and Output timing reference levels: 1.5V
- * Output load: see diagram
- * $V_{CC} = 5V \pm 10\%$

Output Load



Low V_{CC} Data Retention Characteristics - L Version Only ($T_{OP} = 0^{\circ}C$ to $70^{\circ}C$)

Parameter	Symbol	Test Condition	-L Part			Unit
			min	typ	max	
V_{CC} for Data Retention	V_{DR}	$\overline{CS} \geq V_{CC} - 0.2V$ $0.2V \geq V_{in} \geq V_{CC} - 0.2$	2.0	-	-	V
Data Retention Current	I_{CCDR}	$V_{CC} = 3.0V, \overline{CS} = V_{CC} - 0.2V, 0.2V \geq V_{in} \geq V_{CC} - 0.2$	-	-	400	μA
Chip Deselect to Data Ret. Time	t_{CDR}	See Retention Waveform	0	-	-	ns
Operation Recovery Time	t_R	See Retention Waveform	5	-	-	ms

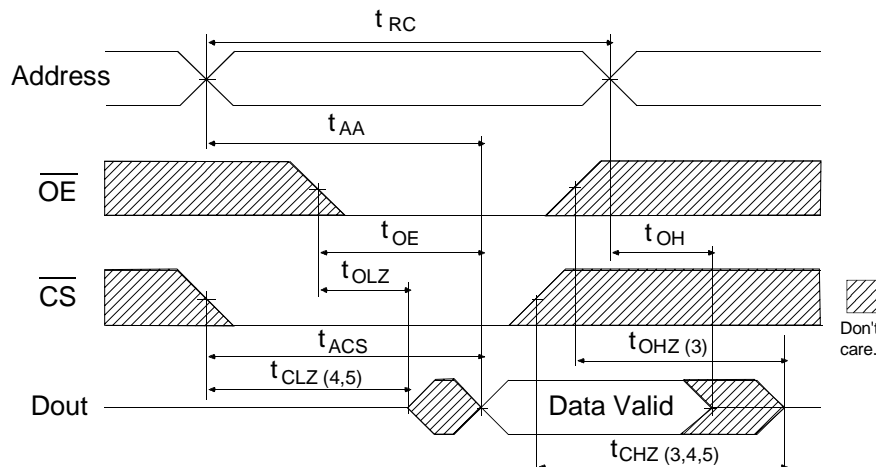
AC OPERATING CONDITIONS**Read Cycle**

Parameter	Symbol	-70		-85		-10		-12		Unit
		min	max	min	max	min	max	min	max	
Read Cycle Time	t_{RC}	70	-	85	-	100	-	120	-	ns
Address Access Time	t_{AA}	-	70	-	85	-	100	-	120	ns
Chip Select Access Time	t_{ACS}	-	70	-	85	-	100	-	120	ns
Output Enable to Output Valid	t_{OE}	-	40	-	45	-	50	-	55	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	10	-	10	-	ns
Chip Selection to Output in Low Z	t_{CLZ}	10	-	10	-	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ}	5	-	5	-	5	-	5	-	ns
Chip Deselection to O/P in High Z	t_{CHZ}	0	30	0	30	0	35	0	40	ns
Output Disable to Output in High Z	t_{OHZ}	0	30	0	30	0	35	0	40	ns

Write Cycle

Parameter	Symbol	-70		-85		-10		-12		Unit
		min	max	min	max	min	max	min	max	
Write Cycle Time	t_{WC}	70	-	85	-	100	-	120	-	ns
Chip Selection to End of Write	t_{CW}	60	-	75	-	80	-	100	-	ns
Address Setup Time	t_{AS}	0	-	0	-	0	-	0	-	ns
Address Valid to End of Write	t_{AW}	60	-	75	-	80	-	100	-	ns
Write Pulse Width	t_{WP}	55	-	65	-	70	-	80	-	ns
Write Recovery Time	t_{WR}	5	-	5	-	5	-	5	-	ns
Write to Output in High Z	t_{WHZ}	0	25	0	30	0	35	0	40	ns
Data to Write Time Overlap	t_{DW}	30	-	35	-	40	-	45	-	ns
Data Hold from Write Time	t_{DH}	0	-	0	-	0	-	0	-	ns
Output active from end of write	t_{OW}	5	-	5	-	5	-	5	-	ns

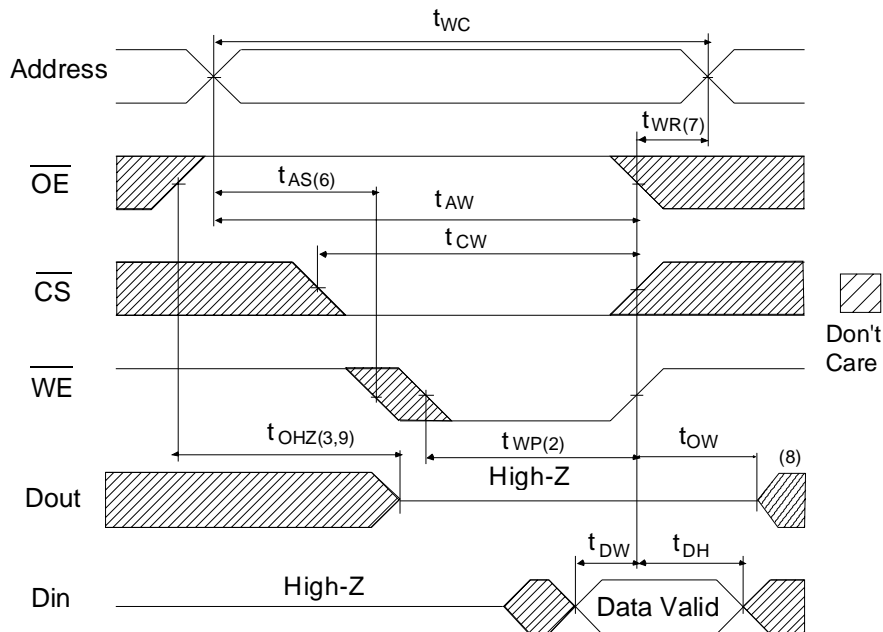
Read Cycle Timing Waveform ^(1,2)



AC Read Characteristics Notes

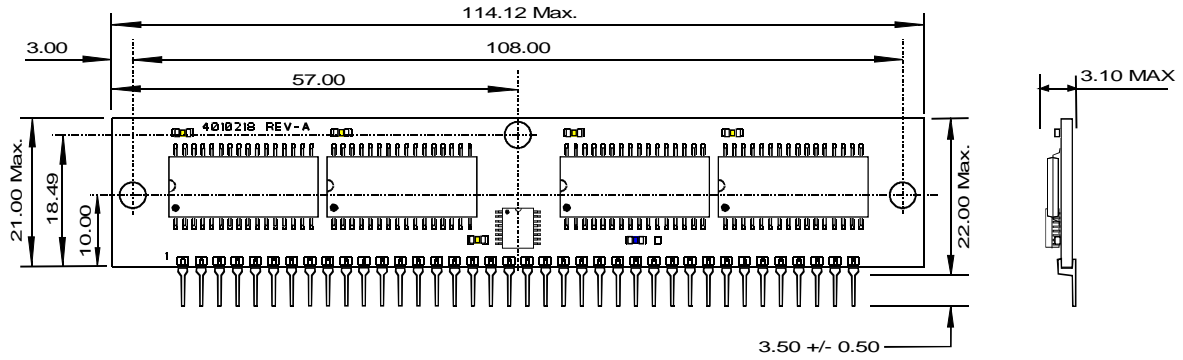
- (1) \overline{WE} is High for Read Cycle.
- (2) All read cycle timing is referenced from the last valid address to the first transition address.
- (3) t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve open circuit conditions and are not referenced to output voltage levels.
- (4) At any given temperature and voltage condition, t_{CHZ} (max) is less than t_{CLZ} (min) both for a given module and from module to module.
- (5) These parameters are sampled and not 100% tested.

Write Cycle No.1 Timing Waveform ^(1,4)



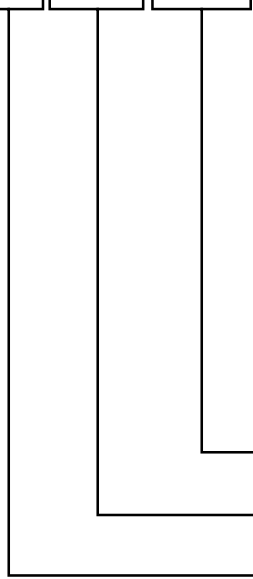
Package Information Dimensions in mm

Plastic 38 Pin Single-In-Line (SIP)



Ordering Information

SYS82000RKXCLI - 70



- Speed
 - 70 = 70 ns
 - 85 = 85 ns
 - 10 = 100 ns
 - 12 = 120 ns
- Temperature Range
 - Blank = Commercial Temperature
 - I = Industrial Temperature
- Power Consumption
 - Blank = Standard Part
 - L = Low Power Part
- Package
 - RKXC = Plastic 38 pin SIP
- Organization
 - 82000 = 2M x 8
- Memory Type
 - SYS = Static RAM

Note :

Although this data is believed to be accurate, the information contained herein, is not intended to and does not create any warranty of merchantability or fitness for a particular purpose. Our products are subject to a constant process of development. Data may be changed at any time without notice. Products are not authorised for use as critical components in life support devices without the express written approval of a company director.